



CST4009S N-Ch 40V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

CST4009S Product Summary

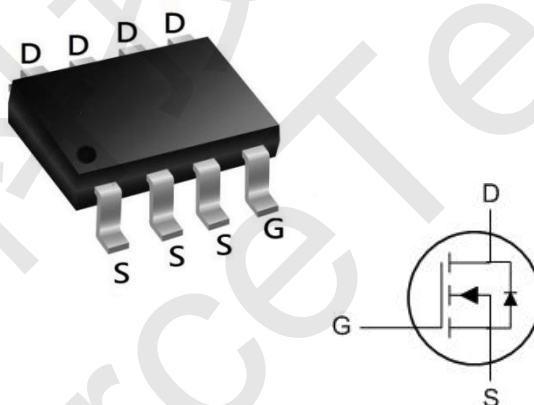


BVDSS	RDSON	ID
40V	12 mΩ	9A

CST4009S Description

The CST4009S is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The CST4009S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

CST4009S SOP8 Pin Configuration



CST4009S Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	9	A
Drain Current-Continuous(T _c =100°C)	I _D (100°C)	6.4	A
Pulsed Drain Current	I _{DM}	40	A
Maximum Power Dissipation	P _D	2	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 150	°C

CST4009S Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	R _{θJA}	62.5	°C/W
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CST4009S N-CH Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =8A	-	12	16	mΩ
		V _{GS} =4.5V, I _D =4A	-	19	24	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =8A	33	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	964	-	PF
Output Capacitance	C _{oss}		-	109	-	PF
Reverse Transfer Capacitance	C _{riss}		-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =2.5Ω V _{GS} =10V, R _{GEN} =3Ω	-	5.5	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	24	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =8A, V _{GS} =10V	-	22.9	-	nC
Gate-Source Charge	Q _{gs}		-	3.5	-	nC
Gate-Drain Charge	Q _{gd}		-	5.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =9A	-	0.8	1.2	V



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CST4009S N- Channel Typical Electrical and Thermal Characteristics (Curves)

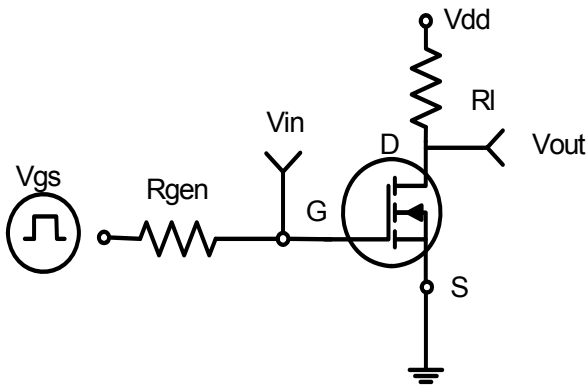


Figure 1: Switching Test Circuit

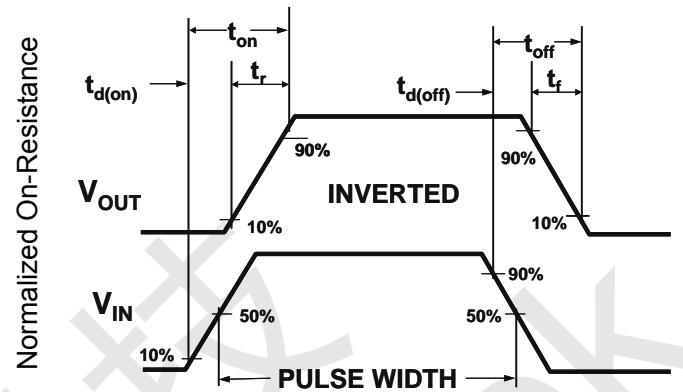


Figure 2: Switching Waveforms

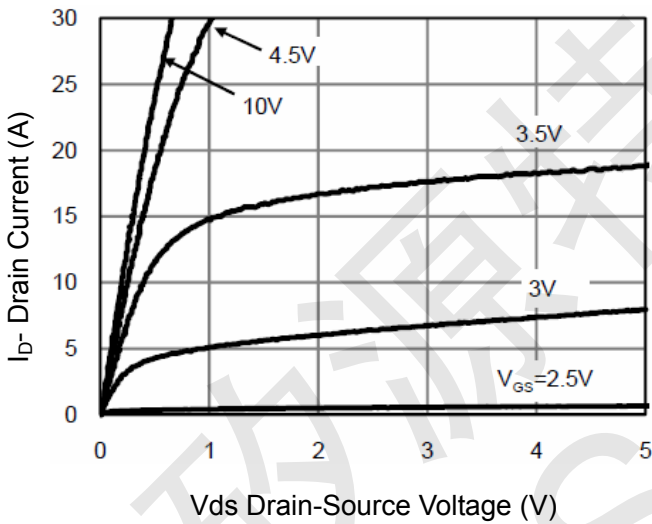


Figure 3 Output Characteristics

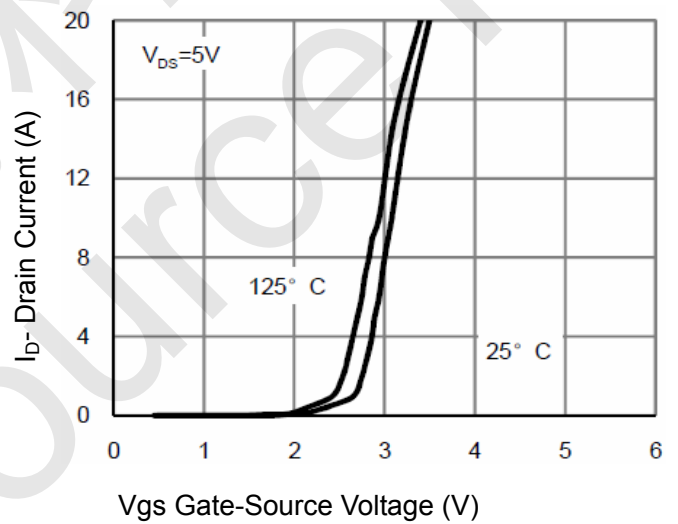


Figure 4 Transfer Characteristics

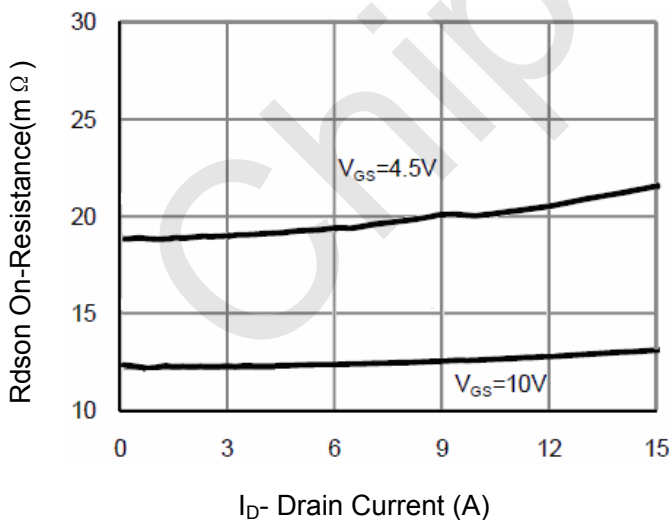


Figure 5 Drain-Source On-Resistance

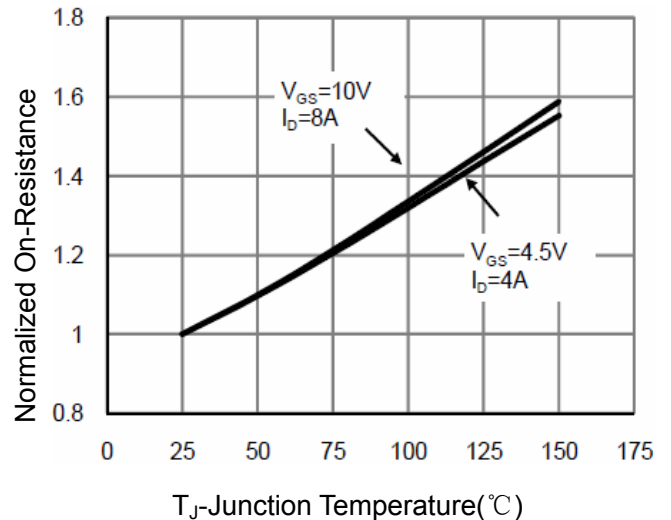


Figure 6 Drain-Source On-Resistance



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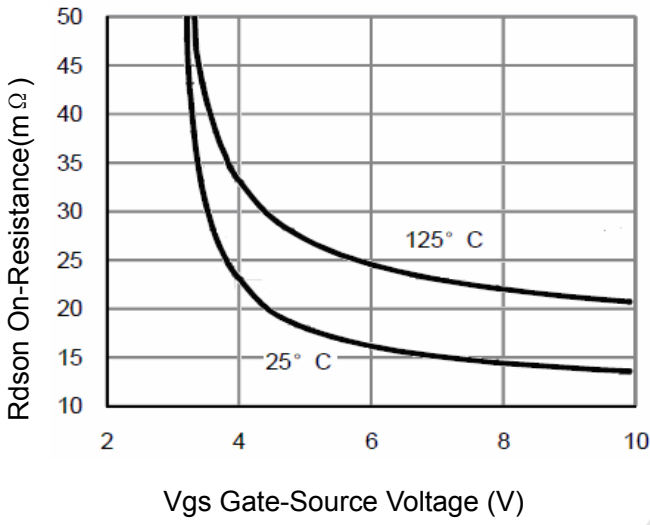


Figure 7 Rdson vs Vgs

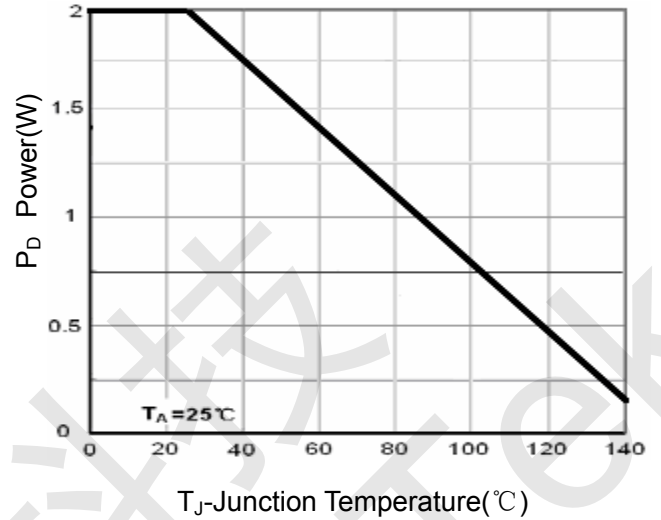


Figure 8 Power Dissipation

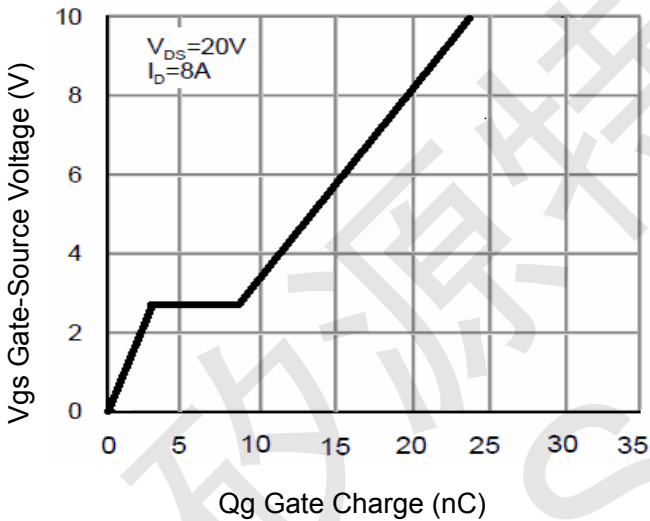


Figure 9 Gate Charge

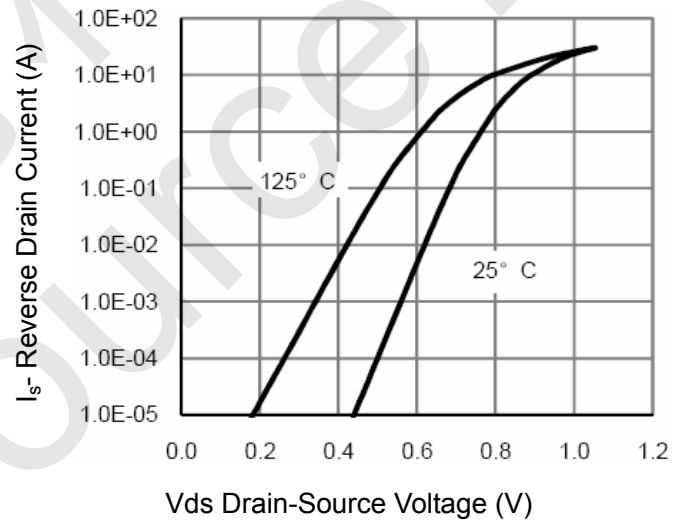


Figure 10 Source- Drain Diode Forward

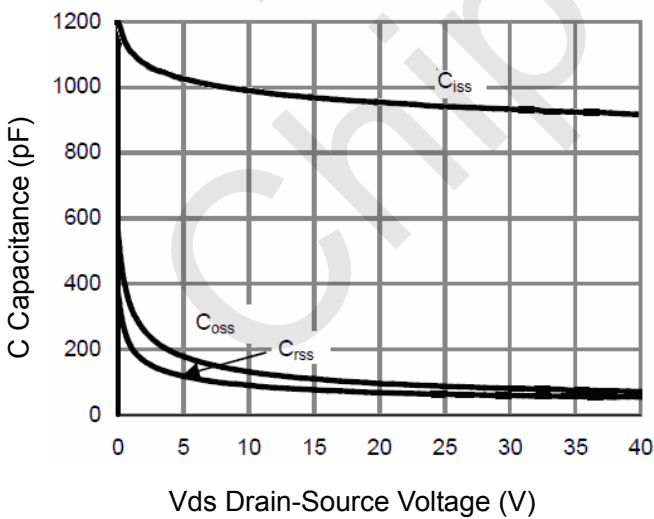


Figure 11 Capacitance vs Vds

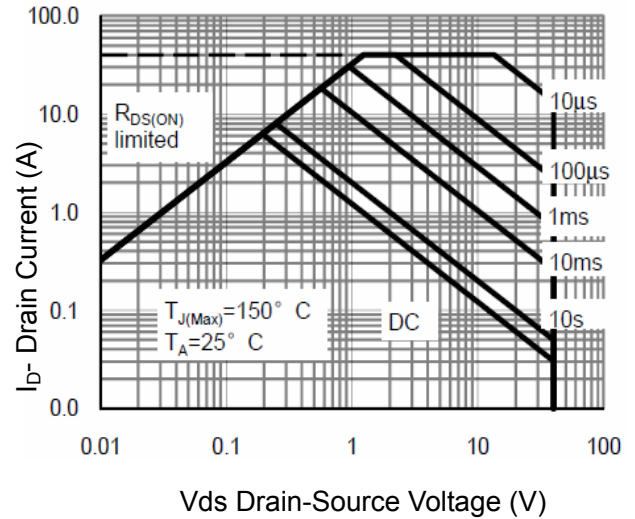


Figure 12 Safe Operation Area



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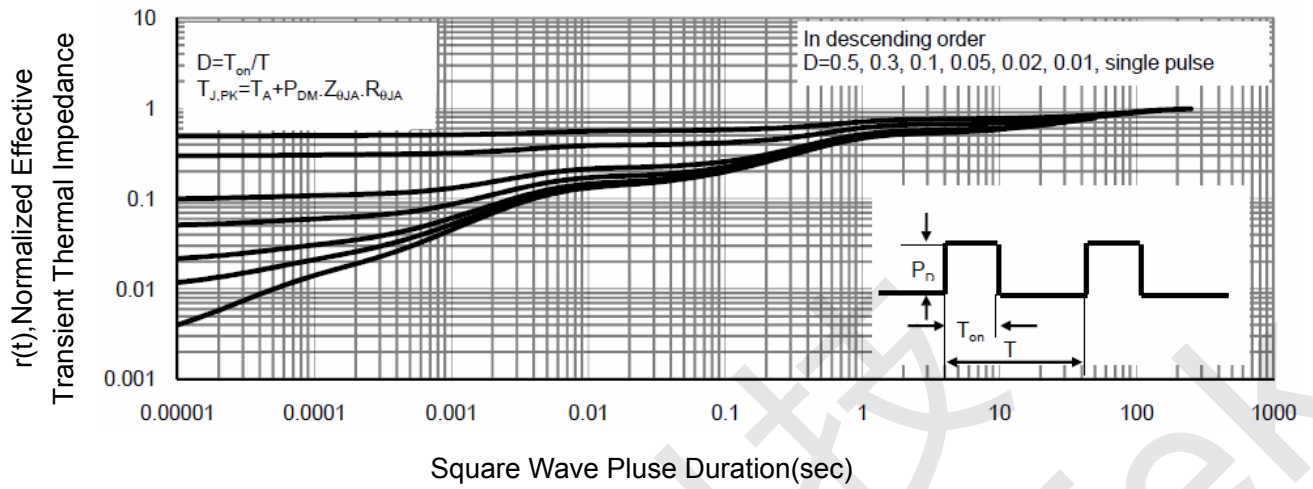
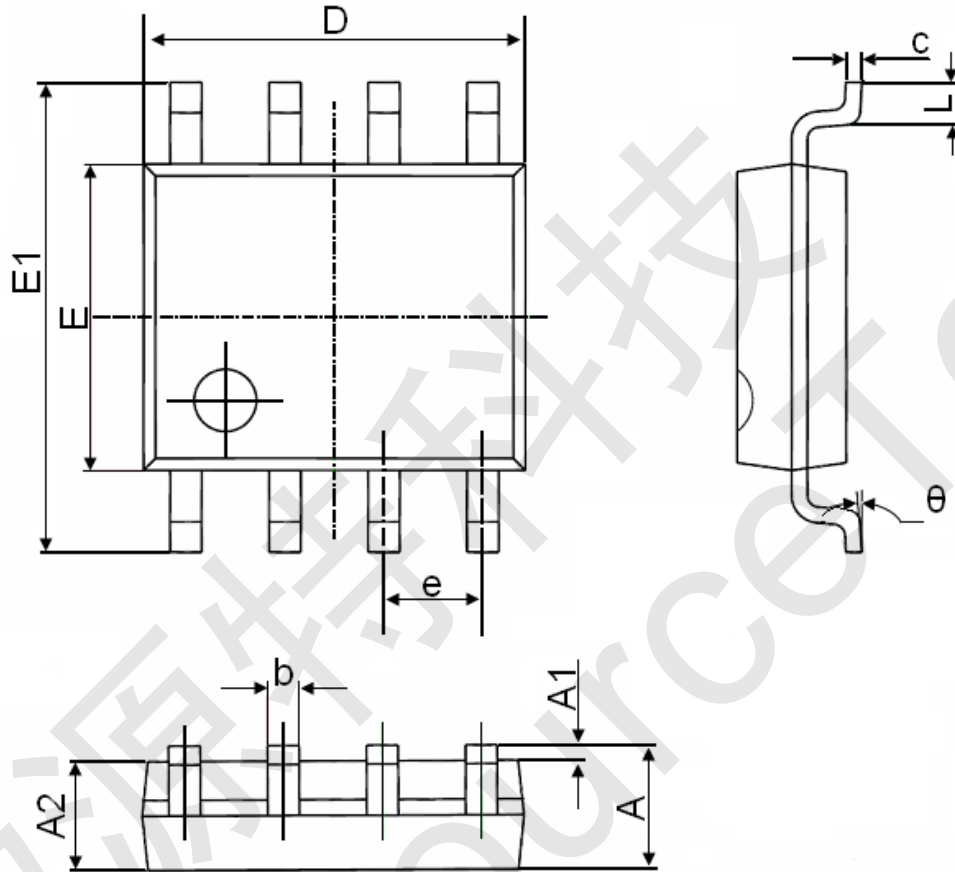


Figure 13 Normalized Maximum Transient Thermal Impedance



CST4009S SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°